TOSHIBA PHOTOCOUPLER GaAℓAs IRED & PHOTO-IC

TLP2200

ISOLATED BUSS DRIVER

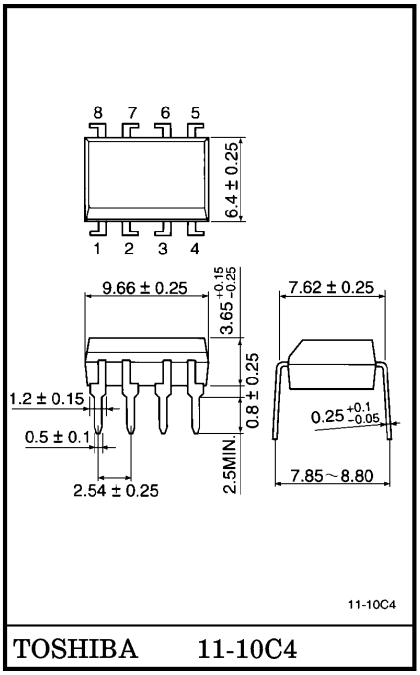
HIGH SPEED LINE RECEIVER

MICROPOCESSOR SYSTEM INTERFACES

MOS FET GATE DRIVER

DIRECT REPLACEMENT FOR HCPL-2200

Unit in mm



TOSHIBA 11-10C4

Weight : 0.54g

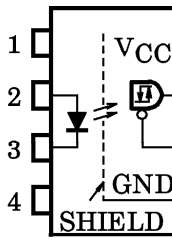
The Toshiba TLP2200 consists of a GaAℓAs light emitting diode and integrated high gain, high speed photodetector.
This unit is 8-lead DIP package.
The detector has a three state output stage that eliminates the need for pull-up resistor, and built-in Schmitt trigger. The detector IC has an internal shield that provides a guaranteed common mode transient immunity of 1000V / μs.

- Input Current : I_F = 1.6mA
- Power Supply Voltage : V_{CC} = 4.5~20V
- Switching Speed : 2.5MBd Guaranteed
- Common Mode Transient Immunity : ±1000V / μs (Min.)
- Guaranteed Performance Over Temp : 0~85°C
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

TRUTH TABLE (Positive logic)

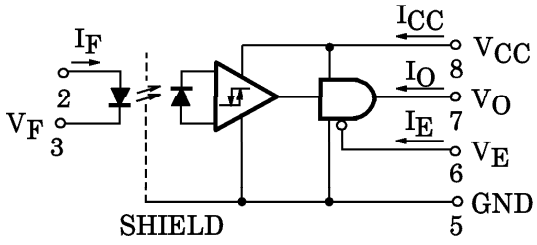
INPUT	ENABLE	OUTPUT
H	H	Z
L	H	Z
H	L	H
L	L	L

PIN CONFIGURATION (Top view)



1 : N.C.
2 : ANODE
3 : CATHODE
4 : N.C.
5 : GND
6 : V_E (ENABLE)
7 : V_O (OUTPUT)
8 : V_{CC}

SCHEMATIC



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input Current, ON	$I_{F\,(ON)}$	1.6	—	5	mA
Input Current, OFF	$I_{F\,(OFF)}$	0	—	0.1	mA
Supply Voltage	V_{CC}	4.5	—	20	V
Enable Voltage High	V_{EH}	2.0	—	20	V
Enable Voltage Low	V_{EL}	0	—	0.8	V
Fan Out (TTL Load)	N	—	—	4	—
Operating Temperature	T_{opr}	0	—	85	°C

ABSOLUTE MAXIMUM RATINGS (No derating required up to 70°C)

	CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current		I_F	10	mA
	Peak Transient Forward Current	(Note 1)	I_{FPT}	1	A
	Reverse Voltage		V_R	5	V
DETECTOR	Output Current		I_O	25	mA
	Supply Voltage		V_{CC}	−0.5~20	V
	Output Voltage		V_O	−0.5~20	V
	Three State Enable Voltage		V_E	−0.5~20	V
	Total Package Power Dissipation	(Note 2)	P_T	210	mW
Operating Temperature Range			T_{opr}	−40~85	°C
Storage Temperature Range			T_{stg}	−55~125	°C
Lead Solder Temperature (10s) (**)			T_{sol}	260	°C
Isolation Voltage (AC 1min., R.H. ≦ 60%, Ta = 25°C) (Note 3)			BV_S	2500	Vrms

(Note 1) Pulse width 1μs 300pps.
(Note 2) Derate 4.5mW / °C above 70°C ambient temperature.
(Note 3) Device considered a two terminal device : pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together
(**) 1.6mm below seating plane.

ELECTRICAL CHARACTERISTICS (Unless otherwise specified, Ta = 0~85°C, V_{CC} = 4.5~20V, $I_{F(ON)}$ = 1.6~5mA, $I_{F(OFF)}$ = 0~0.1mA, V_{EL} = 0~0.8V, V_{EH} = 2.0~20V)

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.*	MAX.	UNIT
Output Leakage Current ($V_O > V_{CC}$)	I_{OHH}	I_F = 5mA, V_{CC} = 4.5V	V_O = 5.5V	—	—	100	μA
			V_O = 20V	—	2	500	
Logic Low Output Voltage	V_{OL}	I_{OL} = 6.4mA (4 TTL load)		—	0.32	0.5	V
Logic High Output Voltage	V_{OH}	I_{OH} = −2.6mA		2.4	3.4	—	V
Logic Low Enable Current	I_{EL}	V_E = 0.4V		—	−0.13	−0.32	mA
Logic High Enable Current	I_{EH}	V_E = 2.7V		—	—	20	μA
		V_E = 5.5V		—	—	100	
		V_E = 20V		—	0.01	250	
Logic Low Enable Voltage	V_{EL}	—		—	—	0.8	V
Logic High Enable Voltage	V_{EH}	—		2.0	—	—	V
Logic Low Supply Current	I_{CCL}	I_F = 0mA, V_E = Don't care	V_{CC} = 5.5V	—	5	6.0	mA
			V_{CC} = 20V	—	5.6	7.5	
Logic High Supply Current	I_{CCH}	I_F = 5mA, V_E = Don't care	V_{CC} = 5.5V	—	2.5	4.5	mA
			V_{CC} = 20V	—	2.8	6.0	
High Impedance State Output Current	I_{OZL}	I_F = 5mA, V_E = 2V	V_O = 0.4V	—	1	−20	μA
	I_{OZH}	I_F = 0mA, V_E = 2V	V_O = 2.4V	—	—	20	
			V_O = 5.5V	—	—	100	
			V_O = 20V	—	0.01	500	
Logic Low Short Circuit Output Current (Note 4)	I_{OSL}	I_F = 0mA	V_O = V_{CC} = 5.5V	25	55	—	mA
			V_O = V_{CC} = 20V	40	80	—	
Logic High Short Circuit Output Current (Note 4)	I_{OSH}	I_F = 5mA, V_O = GND	V_{CC} = 5.5V	−10	−25	—	mA
			V_{CC} = 20V	−25	−60	—	
Input Current Hysteresis	I_{HYS}	V_{CC} = 5V		—	0.05	—	mA
Input Forward Voltage	V_F	I_F = 5mA, Ta = 25°C		—	1.55	1.7	V
Temperature Coefficient of Forward Voltage	$\Delta V_F / \Delta Ta$	I_F = 5mA		—	−2.0	—	mV / °C
Input Reverse Breakdown Voltage	BV_R	I_R = 10μA, Ta = 25°C		5	—	—	V
Input Capacitance	C_{IN}	V_F = 0V, f = 1MHz, Ta = 25°C		—	45	—	pF
Resistance (Input-Output)	R_{I-O}	V_{I-O} = 500V R.H. ≦ 60% (Note 3)		5×10^{10}	10^{14}	—	Ω
Capacitance (Input-Output)	C_{I-O}	V_{I-O} = 0V, f = 1MHz (Note 3)		—	0.6	—	pF

(**) All typ. values are at Ta = 25°C, V_{CC} = 5V, $I_{F(ON)}$ = 3mA unless otherwise specified.

SWITCHING CHARACTERISTICS
(Unless otherwise specified, Ta = 0~85°C, V_{CC} = 4.5~20V, $I_{F\,(ON)}$ = 1.6~5mA, $I_{F\,(OFF)}$ = 0~0.1mA)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Propagation Delay Time to Logic High Output Level (Note 5)	t_{pLH}	1	Without peaking capacitor C_1	—	235	—	ns
			With peaking capacitor C_1	—	—	400	
Propagation Delay Time to Logic Low Output Level (Note 5)	t_{pHL}		Without peaking capacitor C_1	—	250	—	ns
			With peaking capacitor C_1	—	—	400	
Output Rise Time (10-90%)	t_r		—	—	35	—	ns
Output Fall Time (90-10%)	t_f			—	20	—	ns
Output Enable Time to Logic High	t_{pZH}	2	—	—	—	—	ns
Output Enable Time to Logic Low	t_{pZL}		—	—	—	—	ns
Output Disable Time from Logic High	t_{pHZ}		—	—	—	—	ns
Output Disable Time from Logic Low	t_{pLZ}		—	—	—	—	ns
Common Mode Transient Immunity at Logic High Output (Note 6)	CM_H	3	I_F = 1.6mA, V_{CM} = 50V, Ta = 25°C	−1000	—	—	V / μs
Common Mode Transient Immunity at Logic Low Output (Note 6)	CM_L		I_F = 0mA, V_{CM} = 50V, Ta = 25°C	1000	—	—	V / μs

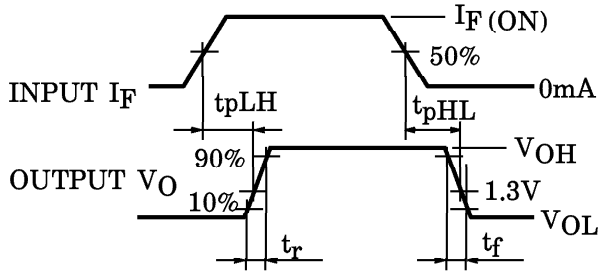
(*) ALL Typ. values are at Ta = 25°C, V_{CC} = 5V, $I_{F\,(ON)}$ = 3mA unless otherwise specified.

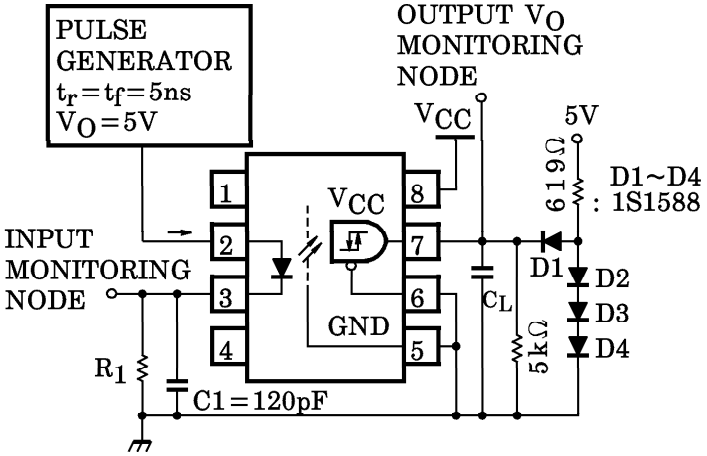
(Note 4) Duration of output short circuit time should not exceed 10ms.

(Note 5) The t_{pLH} propagation delay is measured from the 50% point on the leading edge of the input pulse to the 1.3V point on the leading edge of the output pulse.
The t_{pHL} propagation delay is measured from the 50% point on the trailing edge of the input pulse to the 1.3V point on the trailing edge of the output pulse.

(Note 6) CM_L is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_O \leqq 0.8V$).
CM_H is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic high state ($V_O \leqq 2.0V$).

TEST CIRCUIT 1 t_{pHL}, t_{pLH}, t_r and t_f

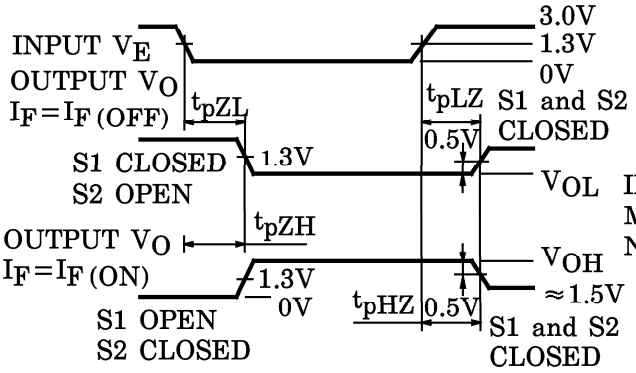


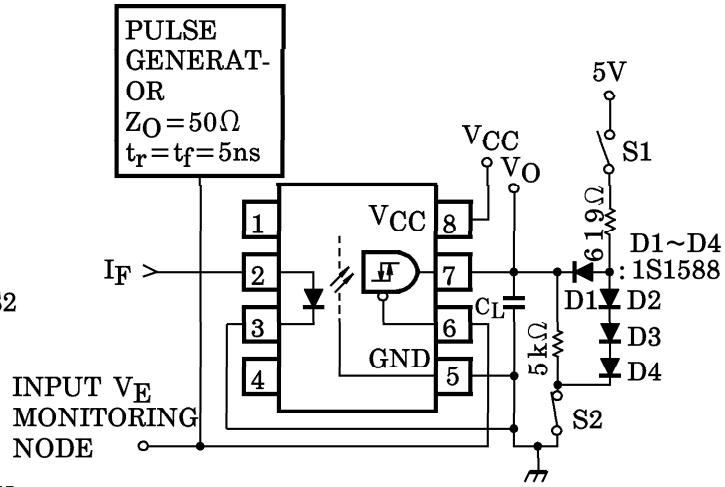


R_1	2.15kΩ	1.1kΩ	681Ω
$I_{F\,(ON)}$	1.6mA	3mA	5mA

C_1 is peaking capacitor. The probe and jig capacitances are include in C_1.
C_L is approximately 15pF which includes probe and stray wiring capacitance.

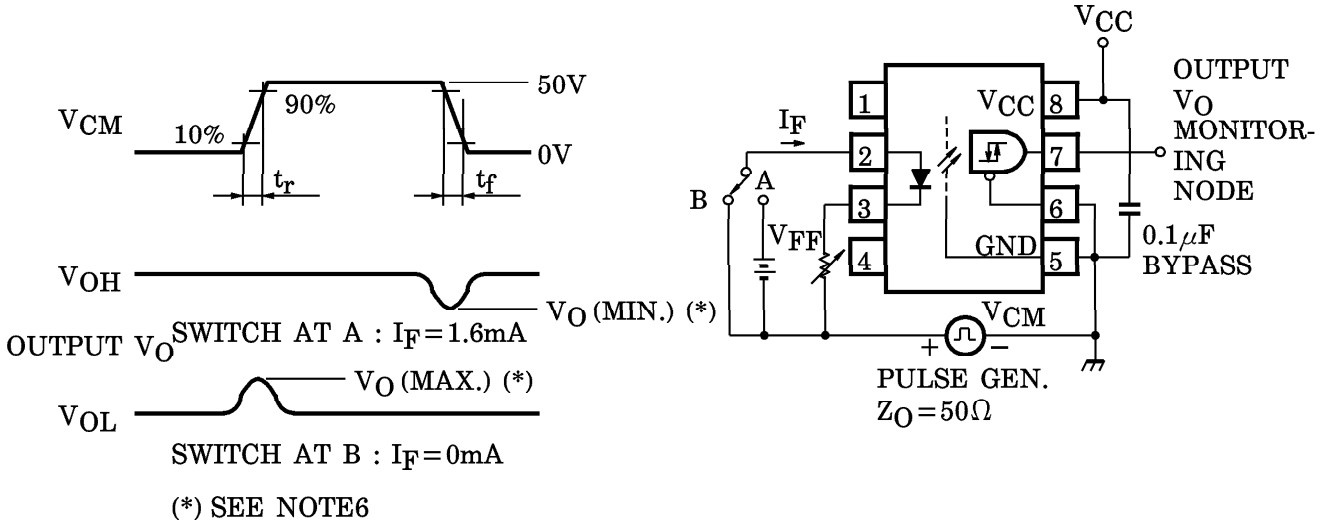
TEST CIRCUIT 2 t_{pHZ}, t_{pZH}, t_{pLZ} and t_{pZL}





C_L is approximately 15pF which includes probe and stray wiring capacitance.

TEST CIRCUIT 3 Common mode transient immunity



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